

Supporting Information

Synthesis, characterization and properties of indium-doped manganese oxide molecular sieve sponges

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Supporting Information Table S1. Comparison and highlight the advantages of this work.

	Sample code	Macroscopic morphology	Electrical resistivity /($\text{k}\Omega \cdot \text{cm}$)	Electrical conductivity /($\text{mS} \cdot \text{cm}^{-1}$)	ICP concentration of indium (wt)
Comparison	M1-powder	powder	0.23	4.34	9.14%
	M2-powder	powder	0.10	10.06	3.03%
	M3-powder	powder	0.05	19.23	5.15%
	M4-powder	powder	0.03	32.26	4.48%
	R-powder	powder	0.72	1.39	0.00%
	M2-sponge	3D foam	0.19	5.19	3.03%
	M3-sponge	3D foam	0.74	1.35	5.15%
	R-sponge	3D foam	0.21	4.72	0.00%
Highlight	Free-standing, macroscopic 3D manganese oxide molecular sieve sponges were prepared.				
	Electrical conductivity of substrates increases by 3-23 times upon indium doping conditions.				
	Indium doping may create two new FT-IR bands at $1090\text{-}1092 \text{ cm}^{-1}$ and $1026\text{-}1028 \text{ cm}^{-1}$.				
	Indium doping may weaken most Raman bands except the band at ca. 640 cm^{-1} .				
	Indium-doped OMS-2 material is electroactive for the catalytic reduction of oxygen.				